

## FUJI POWER MOSFET Super FAP-G Series

## N-CHANNEL SILICON POWER MOSFET

### Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

### Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

### Maximum ratings and characteristic Absolute maximum ratings

(Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V <sub>DS</sub>	900	V
	V <sub>DSX</sub> *5	900	V
Continuous drain current	I <sub>D</sub>	±2.2	A
Pulsed drain current	I <sub>D(puls)</sub>	±8.8	A
Gate-source voltage	V <sub>GS</sub>	±30	V
Repetitive or non-repetitive	I <sub>AR</sub> *2	2.2	A
Maximum Avalanche Energy	E <sub>AS</sub> *1	127.2	mJ
Maximum Drain-Source dV/dt	dV <sub>ps</sub> /dt *4	40	kV/μs
Peak Diode Recovery dV/dt	dV/dt *3	5	kV/μs
Max. power dissipation	P <sub>d</sub>	T <sub>a</sub> =25°C	2.16
		T <sub>c</sub> =25°C	26
Operating and storage temperature range	T <sub>ch</sub>	+150	°C
	T <sub>stg</sub>	-55 to +150	°C
Isolation Voltage	V <sub>ISO</sub> *6	2000	V <sub>rms</sub>

\*1 L=48.2mH, V<sub>CC</sub>=90V, T<sub>ch</sub>=25°C See to Avalanche Energy Graph \*2 T<sub>ch</sub> ≤ 150°C

\*3 I<sub>F</sub> ≤ -I<sub>D</sub>, -di/dt=50A/μs, V<sub>CC</sub> ≤ BV<sub>DSS</sub>, T<sub>ch</sub> ≤ 150°C \*4 V<sub>DS</sub> ≤ 900V \*5 V<sub>GS</sub>=-30V \*6 f=60Hz, t=6-sec.

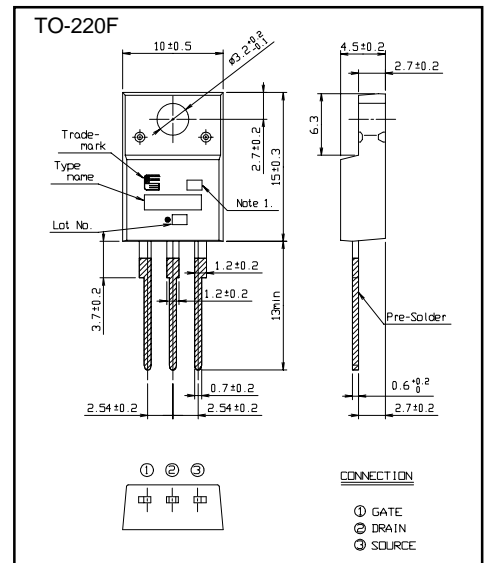
### Electrical characteristics (T<sub>c</sub> =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 250μA V <sub>GS</sub> =0V	900			V
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> = 250μA V <sub>DS</sub> =V <sub>GS</sub>	3.0		5.0	V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =900V V <sub>GS</sub> =0V			25	μA
		V <sub>DS</sub> =720V V <sub>GS</sub> =0V			250	
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V V <sub>DS</sub> =0V			100	nA
Drain-source on-state resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =1.1A V <sub>GS</sub> =10V		6.15	8.00	Ω
Forward transconductance	g <sub>fs</sub>	I <sub>D</sub> =1.1A V <sub>DS</sub> =25V	1.1	2.2		S
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V		250	375	pF
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> =0V		36	55	
Reverse transfer capacitance	C <sub>rss</sub>	f=1MHz		2.2	3.3	
Turn-on time t <sub>on</sub>	td(on)	V <sub>CC</sub> =600V I <sub>D</sub> =1.1A		17	26	ns
	t <sub>r</sub>	V <sub>GS</sub> =10V		6	9	
Turn-off time t <sub>off</sub>	td(off)	R <sub>GS</sub> =10 Ω		26	39	
	t <sub>f</sub>			28	42	
Total Gate Charge	Q <sub>G</sub>	V <sub>CC</sub> =450V		8.3	12.5	nC
Gate-Source Charge	Q <sub>GS</sub>	I <sub>D</sub> =2.2A		3.4	5.1	
Gate-Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> =10V		2.2	3.3	
Avalanche capability	I <sub>AV</sub>	L=48.2mH T <sub>ch</sub> =25°C	2.2			A
Diode forward on-voltage	V <sub>SD</sub>	I <sub>F</sub> =2.2A V <sub>GS</sub> =0V T <sub>ch</sub> =25°C		0.90	1.50	V
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =2.2A V <sub>GS</sub> =0V		0.8		μs
Reverse recovery charge	Q <sub>rr</sub>	-di/dt=100A/μs T <sub>ch</sub> =25°C		2.2		μC

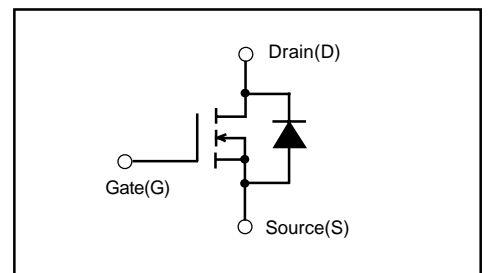
### Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R <sub>th(ch-c)</sub>	channel to case			4.808	°C/W
	R <sub>th(ch-a)</sub>	channel to ambient			58.0	°C/W

### Outline Drawings [mm]



### Equivalent circuit schematic



Characteristics

